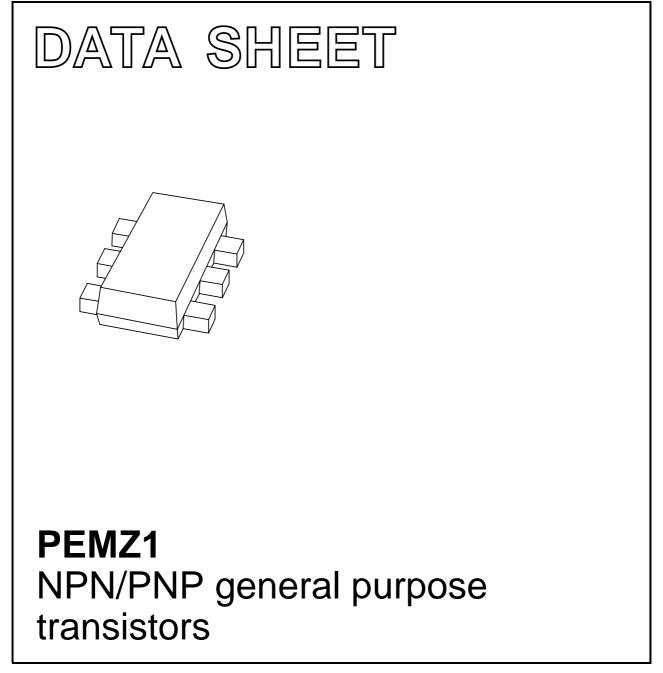
DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 2001 Sep 25 2001 Nov 07



NPN/PNP general purpose transistors

FEATURES

- 300 mW total power dissipation
- Very small 1.6×1.2 mm ultra thin package
- Self alignment during soldering due to straight leads
 Replaces two SC-75/SC-89 packaged transistors on
- Reduced required PCB area
- Reduced pick and place costs.

APPLICATIONS

same PCB area

- General purpose switching and amplification
- Complementary MOSFET driver for switch mode power supply
- Complementary driver for audio amplifiers.

DESCRIPTION

NPN/PNP transistor pair in a SOT666 plastic package.

MARKING

TYPE NUMBER	MARKING CODE		
PEMZ1	FZ		

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transistor; for the PNP transistor with negative polarity					
V _{CBO}	collector-base voltage	open emitter	_	50	V
V _{CEO}	collector-emitter voltage	open base	_	40	V
V _{EBO}	emitter-base voltage	open collector	_	5	V
I _C	collector current (DC)		-	100	mA
I _{CM}	peak collector current		-	200	mA
I _{BM}	peak base current		-	200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$; note 1	-	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb} operating ambient temperature			-65	+150	°C
Per device	•				
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C; note 1$	-	300	mW

2

Note

1. Transistor mounted on an FR4 printed-circuit board.

Fig.1 Simplified outline (SOT666) and symbol.

PINNING

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
6, 3	collector	TR1; TR2	

PEMZ1

NPN/PNP general purpose transistors

PEMZ1

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
R _{th j-a}	thermal resistance from junction to ambient	notes 1 and 2	416	K/W	

Notes

1. Transistor mounted on an FR4 printed-circuit board.

2. The only recommended soldering method is reflow soldering.

CHARACTERISTICS

 T_{amb} = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transis	Per transistor; for the PNP transistor with negative polarity					
I _{CBO}	collector-base cut-off current	$V_{CB} = 30 \text{ V}; \text{ I}_{E} = 0$	_	_	100	nA
		V _{CB} = 30 V; I _E = 0; T _j = 150 °C	_	_	10	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 4 V; I_{C} = 0$	_	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 6 V; I_C = 1 mA$	120	_	_	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = 50 \text{ mA}; I_{B} = 5.0 \text{ mA}; \text{ note 1}$	-	-	200	mV
f _T	transition frequency	$I_{C} = 2 \text{ mA}; V_{CE} = 12 \text{ V}; \text{ f} = 100 \text{ MHz}$	100	_	_	MHz
C _c	collector capacitance	I _E = i _e = 0; V _{CB} = 12 V; f = 1 MHz				
	TR1 (NPN)		_	-	1.5	pF
	TR2 (PNP)		-	-	2.2	pF

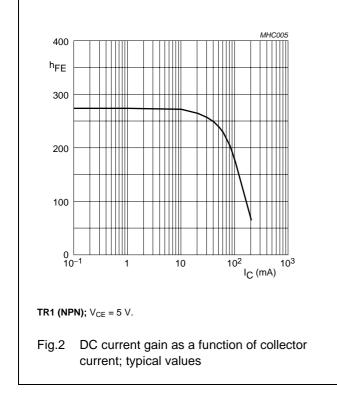
Note

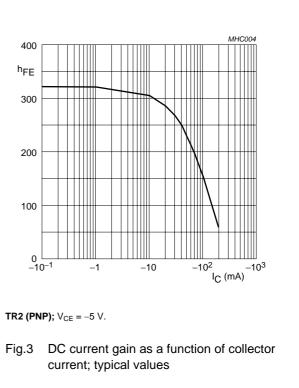
1. Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$

PEMZ1

NPN/PNP general purpose transistors

MHC004





Product data sheet

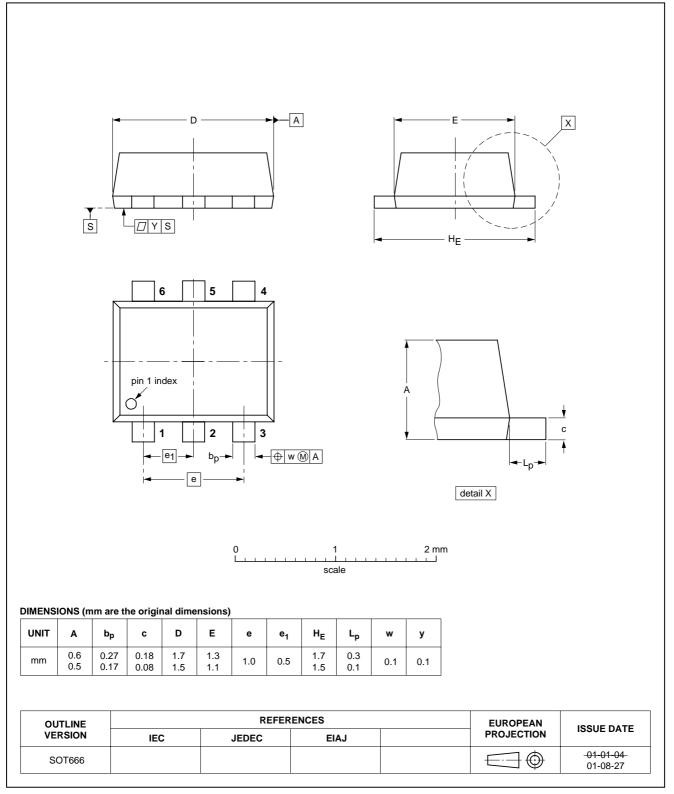
PEMZ1

SOT666

NPN/PNP general purpose transistors

PACKAGE OUTLINE





NPN/PNP general purpose transistors

PEMZ1

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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